







TXS0108E SCES642I - DECEMBER 2007 - REVISED JULY 2023

TXS0108E 8-Bit Bi-directional, Level-Shifting, Voltage Translator for Open-Drain and Push-Pull Applications

1 Features

- No Direction-Control Signal Needed
- Maximum Data Rates
 - 110 Mbps (Push Pull)
 - 1.2 Mbps (Open Drain)
- 1.4 V to 3.6 V on A Port and 1.65 V to 5.5 V on B Port $(V_{CCA} \le V_{CCB})$
- No Power-Supply Sequencing Required Either V_{CCA} or V_{CCB} Can Be Ramped First
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22 (A Port)
 - 2000 V Human Body Model (A114-B)
 - 150 V Machine Model (A115-A)
 - 1000 V Charged-Device Model (C101)
- IEC 61000-4-2 ESD (B Port)
 - ±8 kV Contact Discharge
 - ±6 kV Air-Gap Discharge

2 Applications

- Handsets
- **Smartphones**
- **Tablets**
- Desktop PCs

3 Description

This device is a 8-bit non-inverting level translator which uses two separate configurable power-supply rails. The A port tracks the V_{CCA} pin supply voltage. The V_{CCA} pin accepts any supply voltage between 1.4 V and 3.6 V. The B port tracks the V_{CCB} pin supply voltage. The V_{CCB} pin accepts any supply voltage between 1.65 V and 5.5 V. Two input supply pins allows for low Voltage bidirectional translation between any of the 1.5 V, 1.8 V, 2.5 V, 3.3 V, and 5 V voltage nodes.

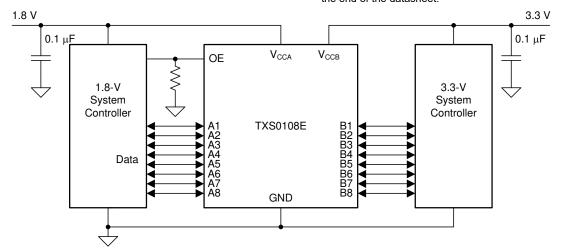
When the output-enable (OE) input is low, all outputs are placed in the high-impedance (Hi-Z) state.

To ensure the Hi-Z state during power-up or powerdown periods, tie OE to GND through a pull-down resistor. The minimum value of the resistor is determined by the current-sourcing capability of the driver.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)								
TXS0108EPW	TSSOP (20)	6.50 mm × 6.40 mm								
TXS0108ERGY	VQFN (20)	4.50 mm × 3.50 mm								
TXS0108EZXY	UFBGA (20)	3.00 mm × 2.50 mm								
TXS0108ENME	NFBGA (20)	3.00 mm × 2.50 mm								

For all available packages, see the orderable addendum at the end of the datasheet.



Simplified Application



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision H (May 2020) to Revision I (July 2023)	Page
Updated the numbering format for tables, figures, and cross-references throughout the document.	1
Changes from Revision G (April 2020) to Revision H (May 2020)	Page
Changed V _{CCB} MAX from 5.5 V to 6.5 V in the <i>Absolute Maximum Ratings</i> table	5
Changes from Revision F (January 2019) to Revision G (April 2020)	Page
Add NME package (NFBGA)	1
Changed V _{CCA} MIN from 1.2 V in the <i>Recommended Operating Conditions</i> table	



5 Pin Configuration and Functions

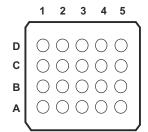


Figure 5-1. ZXY PACKAGE 20 BUMP (BOTTOM VIEW)

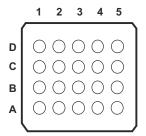


Figure 5-2. NME PACKAGE 20 BGA (BOTTOM VIEW)

Pin Assignments for ZXY and NME Packages

	1	2	3	4	5
D	VCCB	B2	B4	B6	B8
С	B1	В3	B5	B7	GND
В	A1	A3	A5	A7	OE
Α	VCCA	A2	A4	A6	A8

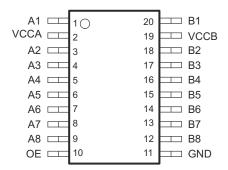
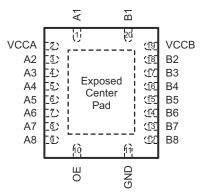


Figure 5-3. PW PACKAGE 20-PIN TSSOP (TOP VIEW)



The exposed center pad, if used, must be connected as a secondary ground or left electrically open.

Figure 5-4. RGY PACKAGE 20 PINS (TOP VIEW)

Pin Functions

	PIN NO.		TYPE ⁽¹⁾	DESCRIPTION					
NAME	PW, RGY	ZXY, NME	I I PE'	DESCRIPTION					
A1	1	B1	I/O	Input/output 1. Referenced to V _{CCA}					
A2	3	A2	I/O	Input/output 2. Referenced to V _{CCA}					
A3	4	B2	I/O	Input/output 3. Referenced to V _{CCA}					
A4	5	A3	I/O	Input/output 4. Referenced to V _{CCA}					
A5	6	В3	I/O	Input/output 5. Referenced to V _{CCA}					
A6	7	A4	I/O	Input/output 6. Referenced to V _{CCA}					
A7	8	B4	I/O	Input/output 7. Referenced to V _{CCA}					
A8	9	A5	I/O	Input/output 8. Referenced to V _{CCA}					
B1	20	C 1	I/O	Input/output 1. Referenced to V _{CCB}					
B2	18	D2	I/O	Input/output 2. Referenced to V _{CCB}					
В3	17	C2	I/O	Input/output 3. Referenced to V _{CCB}					



Pin Functions (continued)

	PIN NO.		TYPE ⁽¹⁾	DESCRIPTION					
NAME	PW, RGY	ZXY, NME	ITPE	DESCRIPTION					
B4	16	D3	I/O	Input/output 4. Referenced to V _{CCB}					
B5	15	C3	I/O	Input/output 5. Referenced to V _{CCB}					
B6	14	D4	I/O	Input/output 6. Referenced to V _{CCB}					
B7	13	C4	I/O	Input/output 7. Referenced to V _{CCB}					
B8	12	D5	I/O	Input/output 8. Referenced to V _{CCB}					
GND	11	C5	_	Ground					
OE	10	B5	I	Tri-state output-mode enable. Pull OE low to place all outputs in 3-state mode. Referenced to V _{CCA} .					
VCCA	2	A1	Р	A-port supply voltage. 1.4 V \leq V _{CCA} \leq 3.6 V, V _{CCA} \leq V _{CCB} .					
VCCB	19	D1	Р	B-port supply voltage. 1.65 V ≤ V _{CCB} ≤ 5.5 V.					
Thermal Pa	ıd		_	For the RGY package, the exposed center thermal pad must be either be connected to Ground or left electrically opened.					

⁽¹⁾ I = input, O = output, I/O = input and output, P = power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT	
Supply voltage, V _{CCA}		-0.5	4.6	V	
Supply voltage, V _{CCB}		-0.5	6.5	V	
Input voltage, V _I ⁽²⁾	A port	-0.5	4.6	V	
input voltage, v ₁ (-)	B port	-0.5	6.5	V	
Voltage applied to any output	A port	-0.5	4.6	V	
in the high-impedance or power-off state, V_{O} (2)	B port	-0.5	6.5	V	
Voltage applied to any output in the high or law state V (2) (3)	A port	-0.5	V _{CCA} + 0.5	V	
Voltage applied to any output in the high or low state, V_{O} $^{(2)}$ $^{(3)}$	B port	-0.5	V _{CCB} + 0.5	V	
Input clamp current, I _{IK}	V _I < 0		-50	mA	
Output clamp current, I _{OK}	V _O < 0		-50	mA	
Continuous output current, I _O		-50	50	mA	
Continuous current through V _{CCA} , V _{CCB} , or GND		-100	100	mA	
Junction temperature, T _J			150	°C	
Storage temperature, T _{stg}		-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The input and output negative Voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V_{CCA} and V_{CCB} are provided in the recommended operating conditions table.

6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	
V _(ESD)	Electrostatic discharge	Machine model (MM)	±150	V
	alconarge	IEC 61000-4-2 ESD (B Port) Contact Discharge	±8000	
		IEC 61000-4-2 ESD (B Port) Air-Gap Discharge	±6000	

⁽¹⁾ JEDEC document JEP155 states that 500 V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ JEDEC document JEP157 states that 250 V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1) (2)

	-		·	,	MIN	MAX	UNIT	
V _{CCA}	Supply voltage ⁽³⁾				1.4	3.6	V	
V _{CCB}	Supply voltage ⁽³⁾				1.65	5.5	V	
		A-Port I/Os	V _{CCA} (V) = 1.4 to 1.95	V _{CCB} (V) = 1.65 to 5.5	V _{CCI} - 0.2	V _{CCI}	V	
\ <u>\</u>	High-level input	A-POIL I/OS	V _{CCA} (V) = 1.95 to 3.6	V _{CCB} (V) = 1.65 to 5.5	V _{CCI} - 0.4	V _{CCI}	V	
V IH	voltage	B-Port I/Os	V _{CCA} (V) = 1.4 to 3.6	V _{CCB} (V) = 1.65 to 5.5	V _{CCI} - 0.4	V _{CCI}	V	
V _{CCB} S V _{IH} H v V _{IL} L v		OE	V _{CCA} (V) = 1.4 to 3.6	V _{CCB} (V) = 1.65 to 5.5	V _{CCA} × 0.65	5.5	V	
I V II			A-Port I/Os	V _{CCA} (V) = 1.4 to 1.95	V _{CCB} (V) = 1.65 to 5.5	0	0.15	V
	Low-level input	A-POIL I/OS	V _{CCA} (V) = 1.95 to 3.6	V _{CCB} (V) = 1.65 to 5.5	0	0.15	V	
V IL	voltage	B-Port I/Os	V _{CCA} (V) = 1.4 to 3.6	V _{CCB} (V) = 1.65 to 5.5	0	0.15	V	
		OE	V _{CCA} (V) = 1.4 to 3.6	V _{CCB} (V) = 1.65 to 5.5	0	V _{CCA} × 0.35	V	
		A-Port I/Os Push-pull	V _{CCA} (V) = 1.4 to 3.6	V _{CCB} (V) = 1.65 to 5.5		10	ns/V	
V _{IH} V _{IL} Δt/Δv	Input transition rise or fall rate	B-Port I/Os Push-pull	V _{CCA} (V) = 1.4 to 3.6	V _{CCB} (V) = 1.65 to 5.5		10	ns/V	
		Control input	V _{CCA} (V) = 1.4 to 3.6	V _{CCB} (V) = 1.65 to 5.5		10	ns/V	
T _A	Operating free-air	temperature			-40	85	°C	

6.4 Thermal Information

			TXS0108E					
THERMAL METRIC ⁽¹⁾			RGY (VQFN)	ZXY (UFBGA)	NME (NFBGA)	UNIT		
		20 PINS	20 PINS	20 PINS	20 PINS			
R _{θJA}	Junction-to-ambient thermal resistance	101.5	34.7	101.5	131.4	°C/W		
R ₀ JC(top)	Junction-to-case (top) thermal resistance	35.9	39.5	35.9	56.5	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	52.4	12.7	52.4	83.2	°C/W		
Ψ_{JT}	Junction-to-top characterization parameter	2.3	0.9	2.3	1.5	°C/W		
ΨЈВ	Junction-to-board characterization parameter	51.9	12.7	51.9	82.6	°C/W		
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	_	7.5	_	_	°C/W		

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report.

 V_{CCI} is the V_{CC} associated with the data input port. V_{CCO} is the V_{CC} associated with the output port. V_{CCA} must be less than or equal to V_{CCB} , and V_{CCA} must not exceed 3.6 V.



6.5 Electrical Characteristics: $T_A = -40$ °C to 85°C

over recommended operating free-air temperature range (unless otherwise noted)(1) (2) (3)

DADAMETED		TEST		0 4 00		Γ _A = 25°C		T _A = -40°C to	85°C	
Р.	ARAMETER	CONDITIONS	V _{CCA} (V)	V _{CCB} (V)	MIN	TYP	MAX	MIN	MAX	UNIT
V _{OHA}	Port A output high voltage	$I_{OH} = -20 \mu A$ $V_{IB} \ge V_{CCB} - 0.4 V$	1.4	1.65 to 5.5	V _{CCA} × 0.67					V
		I _{OL} = 180 μA, V _{IB} ≤ 0.15 V	1.4	1.65 to 5.5					0.4	
.,	Port A output	I _{OL} = 220 μA, V _{IB} ≤ 0.15 V	1.65	1.65 to 5.5					0.4	V
V_{OLA}	low voltage	I _{OL} = 300 μA, V _{IB} ≤ 0.15 V	2.3	1.65 to 5.5					0.4	V
		I _{OL} = 400 μA, V _{IB} ≤ 0.15 V	3	1.65 to 5.5					0.55	
V _{OHB}	Port B output high voltage	$I_{OH} = -20 \mu A,$ $V_{IA} \ge V_{CCA} - 0.2 V$	1.4	1.65 to 5.5	V _{CCB} × 0.67					V
		I_{OL} = 220 μ A, $V_{IA} \le 0.15 \text{ V}$	1.4 to 3.6	1.65					0.4	
V	Port B output	$I_{OL} = 300 \mu A, V_{IA} \le 0.15 V$	1.4 to 3.6	2.3					0.4	V
V_{OLB}	low voltage	I _{OL} = 400 μA, V _{IA} ≤ 0.15 V	1.4 to 3.6	3					0.55	V
		I _{OL} = 620 μA, V _{IA} ≤ 0.15 V	1.4 to 3.6	4.5					0.55	
l _l	Input leakage current	OE: V _I = V _{CCI} or GND	1.4	1.65 to 5.5	-1		1		2	μA
I _{OZ}	High-impedance state output current	A or B port	1.4	1.65 to 5.5	-1		1	-2	2	μΑ
		V _I = V _O = Open, I _O = 0	1.4	1.65 to 5.5		1.5		-2	2	
	V _{CCA} supply		1.5 to 3.6	2.3 to 5.5					2	
I _{CCA}	current		3.6	0					2	μA
			0	5.5					-1	
			1.4	1.65 to 5.5		1.5				
	V _{CCB} supply	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	1.5 to 3.6	2.3 to 5.5					6	
I _{CCB}	current	$V_I = V_O = Open, I_O = 0$	3.6	0					-1	μA
			0	5.5					1.4	
I _{CCA} +	Combined	V _I = V _{CCI} or GND,	1.4	2.3 to 5.5		3				μA
I _{CCB}	supply current	I _O = 0	1.5 to 3.6	2.3 to 5.5					8	
I _{CCZA}	High-impedance state V _{CCA} supply current	V _I = V _O = Open, I _O = 0, OE = GND	1.4	1.65 to 5.5		0.05				μА
I _{CCZB}	High-impedance state V _{CCB} supply current	V _I = V _O = Open, I _O = 0, OE = GND	1.4	1.65 to 5.5		4				μА
C _i	Input capacitance	OE	3.3	3.3		4.5			5.5	pF
	Input-to-output	A port	3.3	3.3		6			7	_
C _{io}	internal capacitance	B port	3.3	3.3		5.5			6	pF

6.6 Timing Requirements: $V_{CCA} = 1.5 V \pm 0.1 V$

over recommended operating free-air temperature range, V_{CCA} = 1.5 V ± 0.1 V (unless otherwise noted)

		V _{CC B} = ' ± 0.15		V _{CC B} = ± 0.2		V _{CC B} = ± 0.3		V _{CC B} = ± 0.5		UNIT	
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
Data rate	Push-pull		40		60		60		50	Mbps	
	Open-drain		2		2		2		2	IVIDPS	

 $[\]begin{array}{ll} \text{(1)} & \text{V_{CCO} is the V_{CC} associated with the output port.} \\ \text{(2)} & \text{V_{CCI} is the V_{CC} associated with the input port.} \\ \text{(3)} & \text{V_{CCA} must be less than or equal to V_{CCB}, and V_{CCA} must not exceed 3.6 V.} \\ \end{array}$



6.6 Timing Requirements: V_{CCA} = 1.5 V ± 0.1 V (continued)

over recommended operating free-air temperature range, V_{CCA} = 1.5 V ± 0.1 V (unless otherwise noted)

			V _{CC B} = 1 ± 0.15		V _{CC B} = ± 0.2		V _{CC B} = ± 0.3		V _{CC B} = ± 0.5		UNIT	
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _w	Pulse	Data inputs	Push-pull	25		16.7		16.7		20		ns
	duration	Data Inputs	Open-drain	500		500		500		500		1115

6.7 Timing Requirements: V_{CCA} = 1.8 V ± 0.15 V

over recommended operating free-air temperature range, V_{CCA} = 1.8 V ± 0.15 V (unless otherwise noted)

			V _{CC B} = 1 ± 0.15		V _{CC B} = 2 ± 0.2		V _{CC B} = ± 0.3		V _{CC B} = ± 0.5		UNIT	
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX			
	Data rata	Push-pull			40		60		60		60	Mbps
	Data rate Open-drain				2		2		2		2	IVIDPS
	Pulse	Data inputs Push-pull		25		16.7		16.7		16.7		ns
\w	duration	Data inputs	Open-drain	500		500		500		500		115

6.8 Timing Requirements: V_{CCA} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range, V_{CCA} = 2.5 V ± 0.2 V (unless otherwise noted)

				V _{CCB} = 2.9 ± 0.2 V		V _{CCB} = 3. ± 0.3 \		V _{CC} = 5 ± 0.5 \		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
	Data rata	Push-pull		60		60		60	Mhna	
	Data rate	Open-drain			2		2		2	Mbps
	Pulse duration Data inputs		Push-pull	16.7		16.7		16.7		no
lw	Fuise duration	Data iriputs	Open-drain	500		500		500		ns

6.9 Timing Requirements: $V_{CCA} = 3.3 \text{ V} \pm 0.3 \text{ V}$

over recommended operating free-air temperature range, V_{CCA} = 3.3 V ± 0.3 V (unless otherwise noted)

				V _{CCB} = 3.3 V ± 0.3 V	′	V _{CC} = 5 V ± 0.5 V		UNIT
				MIN	MAX	MIN	MAX	
	Data rate	Push-pull			60		60	Mhna
	Dala Tale	Open-drain			2		2	Mbps
	Pulse duration	Data inputs	Push-pull	16.7		16.7		ne
l'w	, Pulse duration Data Inputs		Open-drain	500		500	ns	



6.10 Switching Characteristics: V_{CCA} = 1.5 V ± 0.1 V

over recommended operating free-air temperature range, V_{CCA} = 1.5 V ± 0.1 V (unless otherwise noted)

	PARAMETER	TEST C	ONDITIONS	V _{CCB} = 1 ± 0.15		V _{CCB} = 2 ± 0.2		V _{CCB} = ± 0.3		V _{CCB} = ± 0.5		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Propagation		Push-pull driving		11	,	9.2		8.6		8.6	
t _{PHL}	delay time (high-to-low output)	A-to-B	Open-drain driving	4	14.4	3.6	12.8	3.5	12.2	3.5	12	ns
	Propagation		Push-pull driving		12		10		9.8		9.7	115
t _{PLH}	delay time (low-to-high output)	A-to-B	Open-drain driving	182	720	143	554	114	473	81	384	
	Propagation		Push-pull driving		12.7		11.1		11		12	
t _{PHL}	delay time (high-to-low output)	B-to-A	Open-drain driving	3.4	13.2	3.1	9.6	2.8	8.5	2.5	7.5	ns
	Propagation		Push-pull driving		9.5		6.2		5.1		1.6	115
t _{PLH}	delay time (low-to-high output)	B-to-A	Open-drain driving	186	745	147	603	118	519	84	407	
t _{en}	Enable time	OE-to-A or B	Push-pull driving		200		200		200		200	ns
t _{dis}	Disable time	OE-to-A or B	Push-pull driving		28.1		22		20.1		19.6	ns
	Input rise time	A-port rise time	Push-pull driving	3.5	13.1	3	9.8	3.1	9	3.2	8.3	no
t _{rA}	input rise time	A-port rise time	Open-drain driving	147	982	115	716	92	592	66	481	ns
	Input rise time	B-port rise time	Push-pull driving	2.9	11.4	1.9	7.4	0.9	4.7	0.7	2.6	ns
t _{rB}	input rise time	B-port rise time	Open-drain driving	135	1020	91	756	58	653	20	370	115
	Input fall time	A-port fall time	Push-pull driving	2.3	9.9	1.7	7.7	1.6	6.8	1.7	6	
t _{fA}	input fall time	A-port fail time	Open-drain driving	2.4	10	2.1	7.9	1.7	7	1.5	6.2	
	langet fall time	D next fell time	Push-pull driving	2	8.7	1.3	5.5	0.9	3.8	0.8	3.1	ns
t _{fB}	Input fall time	B-port fall time	Open-drain driving	1.2	11.5	1.3	8.6	1	9.6	0.5	7.7	
t _{SK(O)}	Skew (time), output	Channel-to- channel skew	Push-pull driving		1	1	1		1.1		1	ns
	Maximum	A D	Push-pull driving	40		60		60		50		N41
	data rate	A or B	Open-drain driving	2		2		2		2		Mbps



6.11 Switching Characteristics: V_{CCA} = 1.8 V ± 0.15 V

over recommended operating free-air temperature range, V_{CCA} = 1.8 V \pm 0.15 V (unless otherwise noted)

P/	ARA-METER	TEST CO	NDITIONS	V _{CCB} = 1 ± 0.15	.8 V	V _{CCB} = 2 ± 0.2		V _{CCB} = 3. ± 0.3 V		V _{CCB} = ± 0.5	5 V V	UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t	Propagation delay time	A-to-B	Push-pull driving		8.2		6.4		5.7		5.6	
t _{PHL}	(high-to-low output)	А-то-Б	Open-drain driving	3.6	11.4	3.2	9.9	3.1	9.3	3.1	8.9	ns
t _{PLH}	Propagation delay time	A-to-B	Push-pull driving		9		2.1		6.5		6.3	113
PLH	(low-to-high output)	А-то-Б	Open-drain driving	194	729	155	584	126	466	90	346	
t	Propagation delay time	B-to-A	Push-pull driving		9.8		8		7.4		7	
t _{PHL}	(high-to-low output)	B-10-A	Open-drain driving	3.4	12.1	2.8	8.5	2.5	7.3	2.1	6.2	ns
	Propagation delay time	B-to-A	Push-pull driving		10.2		7		5.8		5	115
t _{PLH}	(low-to-high output)	B-10-A	Open-drain driving	197	733	159	578	129	459	93	323	
t _{en}	Enable time	OE-to-A or B	Push-pull driving		200		200		200		200	ns
t _{dis}	Disable time	OE-to-A or B	Push-pull driving		25.1		18.8		16.5		15.3	ns
		A t i t i	Push-pull driving	3.1	11.9	2.6	8.6	2.7	7.8	2.8	7.2	
t _{rA}	Input rise time	A-port rise time	Open-drain driving	155	996	124	691	100	508	72	350	ns
		D ti ti	Push-pull driving	2.8	10.5	1.8	7.2	1.2	5.2	0.7	2.7	
t _{rB}	Input rise time	B-port rise time	Open-drain driving	132	1001	106	677	73	546	32	323	ns
	L	A	Push-pull driving	2.1	8.8	1.6	6.6	1.4	5.7	1.4	4.9	
t _{fA}	Input fall time	A-port fall time	Open-drain driving	2.2	9	1.7	6.7	1.4	5.8	1.2	5.2	
	L	D	Push-pull driving	2	8.3	1.3	5.4	0.9	3.9	0.7	3	ns
t _{fB}	Input fall time	B-port fall time	Open-drain driving	0.8	10.5	0.7	10.7	1	9.6	0.6	7.8	
t _{SK(O)}	Skew (time), output	Channel-to- channel skew	Push-pull driving		1		1		1		1	ns
	Maximum	A D	Push-pull driving	40		60		60		60		N AL
	data rate	A or B	Open-drain driving	2		2		2		2		Mbps



6.12 Switching Characteristics: $V_{CCA} = 2.5 V \pm 0.2 V$

over recommended operating free-air temperature range, V_{CCA} = 2.5 V \pm 0.2 V (unless otherwise noted)

PA	ARA-METER	TEST CO	NDITIONS	V _{CCB} = 2. ± 0.2 V		V _{CCB} = 3. ± 0.3 V		V _{CCB} = ± 0.5		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
t _{PHL}	Propagation delay time	A -to-B	Push-pull driving		5		4		3.7	
PHL	(high-to-low output)	7. 10 5	Open-drain driving	2.4	6.9	2.3	6.3	2.2	5.8	ns
	Propagation delay time	A to D	Push-pull driving		5.2		4.3		3.9	115
t _{PLH}	(low-to-high output)	A -to-B	Open-drain driving	149	592	125	488	93	368	
4	Propagation delay time	B-to-A	Push-pull driving		5.4		4.7		4.2	
t _{PHL}	(high-to-low output)	Б-10-А	Open-drain driving	2.5	7.3	2.2	6	1.8	4.9	-
4	Propagation delay time	B-to-A	Push-pull driving		5.9		4.4		3.5	ns
t _{PLH}	(low-to-high output)	B-10-A	Open-drain driving	150	595	126	481	94	345	
t _{en}	Enable time	OE-to-A or B	Push-pull driving		200		200		200	ns
t _{dis}	Disable time	OE-to-A or B	Push-pull driving		15.7		12.9		11.2	ns
	In most vice a time a	A	Push-pull driving	2	7.3	2.1	6.4	2.2	5.8	
t _{rA}	Input rise time	A-port rise time	Open-drain driving	110	692	93	529	68	369	ns
			Push-pull driving	1.8	6.5	1.3	5.1	0.7	3.4	
t _{rB}	Input rise time	B-port rise time	Open-drain driving	107	693	79	483	41	304	ns
	loon of fall times	A and fall dines	Push-pull driving	1.5	5.7	1.2	4.7	1.3	3.8	
t _{fA}	Input fall time	A-port fall time	Open-drain driving	1.5	5.6	1.2	4.7	1.1	4	
4	Input fall times	D post fell times	Push-pull driving	1.4	5.4	0.9	4.1	0.7	3	ns
t _{fB}	Input fall time	B-port fall time	Open-drain driving	0.4	14.2	0.5	19.4	0.4	3	
t _{SK(O)}	Skew (time), output	Channel-to- channel skew	Push-pull driving		1		1.2		1	ns
	Maximum	A an B	Push-pull driving	60		60		60		N.41
	data rate	A or B	Open-drain driving	2		2		2		Mbps



6.13 Switching Characteristics: V_{CCA} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, V_{CCA} = 3.3 V \pm 0.3 V (unless otherwise noted)

	PARAMETER	TES	T CONDITIONS	V _{CCB} = 3.3 \ ± 0.3 V	/	V _{CCB} = 5 V ± 0.5 V	'	UNIT
				MIN	MAX	MIN	MAX	
	Propagation		Push-pull driving		3.8		3.1	
t _{PHL}	delay time (high-to-low output)	A-to-B	Open-drain driving	2	5.3	1.9	4.8	
	Propagation		Push-pull driving		3.9		3.5	ns
t _{PLH}	delay time (low-to-high output)	A-to-B	Open-drain driving	111	439	87	352	
_	Propagation		Push-pull driving		4.2		3.8	
t _{PHL}	delay time (high-to-low output)	B-to-A	Open-drain driving	2.1	5.5	1.7	4.5	
	Propagation		Push-pull driving		3.8		4.3	ns
t _{PLH}	delay time (low-to-high output)	A-to-B	Open-drain driving	112	449	86	339	
t _{en}	Enable time	OE-to-A or B	Push-pull driving		200		200	ns
t _{dis}	Disable time	OE-to-A or B	Push-pull driving		11.9		9.8	ns
+ .	Input rise time	A-port rise time	Push-pull driving	1.8	5.7	1.9	5	ns
t _{rA}	input rise time	A-port rise time	Open-drain driving	75	446	57	337	115
t _	Input rise time	B-port rise time	Push-pull driving	1.5	5	1	3.6	ns
t _{rB}	input rise time	b-port rise time	Open-drain driving	72	427	40	290	115
+	Input fall time	A-port fall time	Push-pull driving	1.2	4.5	1.1	3.5	
t _{fA}	input iali time	A-port fail time	Open-drain driving	1.1	4.4	1	3.7	ns
+_	Input fall time	B-port fall time	Push-pull driving	1.1	4.2	0.8	3.1	115
t _{fB}	input iali time	b-port fail time	Open-drain driving	1	4.2	0.8	3.1	
t _{SK(O)}	Skew (time), output	Channel-to- channel skew	Push-pull driving		1		1	ns
	Maximum data rate	A or B	Push-pull driving	60		60		Mbps
	waxiiiluiii data iate	AOID	Open-drain driving	2		2		wips

6.14 Operating Characteristics: V_{CCA} = 1.5 V to 3.3 V, V_{CCB} = 1.5 V to 3.3 V

 $T_{\Lambda} = 25^{\circ}C$

i A	25 C			Vcc	_A = 1.	5 V,	Vcc	_{:A} = 1.8	3 V,	Vcc	_{CA} = 2.	5 V,	V _c	_{CA} = 2.	5 V,	V	_{CCA} = 3	.3 V,	
ΡΔ	RAMETER	TEST C	ONDITIONS		B = 1.			B = 1.8			_{CB} = 2.			_{CB} = 2.			_{CCB} = 3		UNIT
			ONDITIONO	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MI N	TYP	MAX	Oilli
6	Power dissipation	CL = 0 f = 10	A-port input, B-port output		5.9			5.9			6.7			6.9			8		
C _{pdA}	capacitanc e	MHz tr= tf= 1	B-port input, A-port output		9.9			9.7			9.7			9.4			9.8		<u>.</u>
_	Power dissipation	ns OE = V _{CCA}	A-port input, B-port output		21.5			20.8			21			23.4			23		pF
C _{pdB}	capacitanc e	(outputs enabled)	B-port input, A-port output		16.7			16.8			17.8			20.8			20.9		
_	Power dissipation	CL = 0 f = 10	A-port input, B-port output		0.01			0.01			0.01			0.01			0.01		
C _{pdA}	capacitanc e	MHz tr= tf= 1	B-port input, A-port output		0.01			0.01			0.01			0.01			0.01		pF
6	Power dissipation	ns OE = V _{CCA}	A-port input, B-port output		0.01			0.01			0.01			0.03			0.02		þΓ
C _{pdB}	capacitanc e	(outputs enabled)	B-port input, A-port output		0.01			0.01			0.01			0.03			0.02		

7 Typical Characteristics

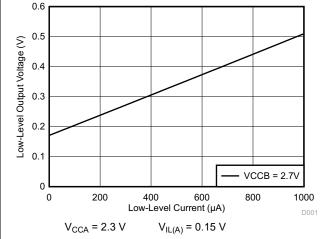


Figure 7-1. Low-Level Output Voltage $(V_{OL(Bx)})$ vs Low-Level Current $(I_{OL(Bx)})$

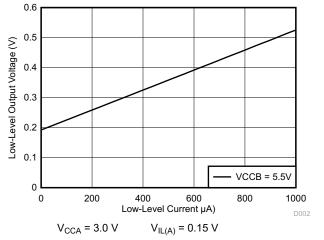


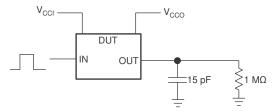
Figure 7-2. Low-Level Output Voltage $(V_{OL(Bx)})$ vs Low-Level Current $(I_{OL(Bx)})$



8 Parameter Measurement Information

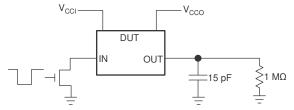
8.1 Load Circuits

Figure 8-1 shows the push-pull driver circuit used for measuring data rate, pulse duration, propagation delay, output rise-time and fall-time. Figure 8-2 shows the open-drain driver circuit used for measuring data rate, pulse duration, propagation delay, output rise-time and fall-time.



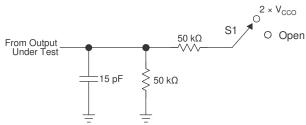
- A. V_{CCI} is the V_{CC} associated with the input port.
- B. V_{CCO} is the V_{CC} associated with the output port.

Figure 8-1. Data Rate, Pulse Duration, Propagation Delay, Output Rise-Time And Fall-Time Measurement Using a Push-Pull Driver



- A. V_{CCI} is the V_{CC} associated with the input port.
- B. V_{CCO} is the V_{CC} associated with the output port.

Figure 8-2. Data Rate (10 pF), Pulse Duration (10 pF), Propagation Delay, Output Rise-Time And Fall-Time Measurement Using an Open-Drain Driver



TEST	S1
t_{PZL},t_{PLZ} (t_{dis})	2 × V _{CCO}
t _{PHZ} , t _{PZH} (t _{en})	Open

- A. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- B. t_{PZL} and t_{PZH} are the same as t_{en} .

Figure 8-3. Load Circuit for Enable-Time and Disable-Time Measurement



8.2 Voltage Waveforms

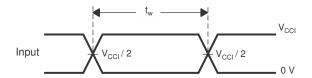


Figure 8-4. Pulse Duration (Push-Pull)

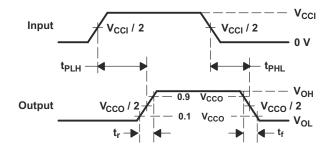


Figure 8-5. Propagation Delay Times



9 Detailed Description

9.1 Overview

The TXS0108E device is a directionless voltage-level translator specifically designed for translating logic voltage levels. The A-port accepts I/O voltages ranging from 1.4 V to 3.6 V. The B-port accepts I/O voltages from 1.65 V to 5.5 V. The device uses pass gate architecture with edge rate accelerators (one shots) to improve the overall data rate. The pull-up resistors, commonly used in open-drain applications, have been conveniently integrated so that an external resistor is not needed. While this device is designed for open-drain applications, the device can also translate push-pull CMOS logic outputs.

9.2 Functional Block Diagram

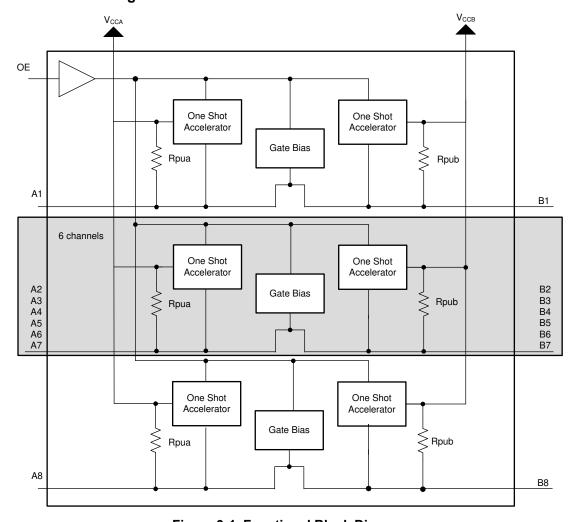


Figure 9-1. Functional Block Diagram

Each A-port I/O has a pull-up resistor (R_{PUA}) to V_{CCA} and each B-port I/O has a pull-up resistor (R_{PUB}) to V_{CCB} . R_{PUA} and R_{PUB} have a value of 40 k Ω when the output is driving low. R_{PUA} and R_{PUB} have a value of 4 k Ω when the output is driving high. R_{PUA} and R_{PUB} are disabled when OE = Low.

9.3 Feature Description

9.3.1 Architecture

Figure 9-2 describes semi-buffered architecture design this application requires for both push-pull and open-drain mode. This application uses edge-rate accelerator circuitry (for both the high-to-low and low-to-high edges), a high-on-resistance N-channel pass-gate transistor (on the order of 300 Ω to 500 Ω) and pull-up resistors (to provide DC-bias and drive capabilities) to meet these requirements. This design needs no direction-control signal (to control the direction of data flow from A to B or from B to A). The resulting implementation supports both low-speed open-drain operation as well as high-speed push-pull operation.

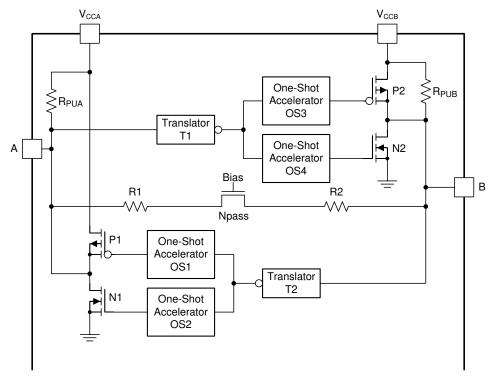


Figure 9-2. Architecture of a TXS0108E Cell

When transmitting data from A-ports to B-ports, during a rising edge the one-shot circuit (OS3) turns on the PMOS transistor (P2) for a short-duration which reduces the low-to-high transition time. Similarly, during a falling edge, when transmitting data from A to B, the one-shot circuit (OS4) turns on the N-channel MOSFET transistor (N2) for a short-duration which speeds up the high-to-low transition. The B-port edge-rate accelerator consists of one-shot circuits OS3 and OS4. Transistors P2 and N2 and serves to rapidly force the B port high or low when a corresponding transition is detected on the A port.

When transmitting data from B- to A-ports, during a rising edge the one-shot circuit (OS1) turns on the PMOS transistor (P1) for a short-duration which reduces the low-to-high transition time. Similarly, during a falling edge, when transmitting data from B to A, the one-shot circuit (OS2) turns on NMOS transistor (N1) for a short-duration and this speeds up the high-to-low transition. The A-port edge-rate accelerator consists of one-shots OS1 and OS2, transistors P1 and N1 components and form the edge-rate accelerator and serves to rapidly force the A port high or low when a corresponding transition is detected on the B port.



9.3.2 Input Driver Requirements

The continuous DC-current *sinking* capability is determined by the external system-level open-drain (or push-pull) drivers that are interfaced to the TXS0108E I/O pins. Because the high bandwidth of these bidirectional I/O circuits is used to facilitate this fast change from an input to an output and an output to an input, they have a modest DC-current *sourcing* capability of hundreds of micro-amperes, as determined by the internal pull-up resistors.

The fall time (t_{fA} , t_{fB}) of a signal depends on the edge-rate and output impedance of the external device driving TXS0108E data I/Os, as well as the capacitive loading on the data lines.

Similarly, the t_{PHL} and maximum data rates also depend on the output impedance of the external driver. The values for t_{fA} , t_{fB} , t_{PHL} , and maximum data rates in the data sheet assume that the output impedance of the external driver is less than 50 Ω .

9.3.3 Output Load Considerations

TI recommends careful PCB layout practices with short PCB trace lengths to avoid excessive capacitive loading and to ensure that proper one-shot triggering takes place. PCB signal trace-lengths should be kept short enough such that the round trip delay of any reflection is less than the one-shot duration. This improves signal integrity by ensuring that any reflection sees a low impedance at the driver. The one-shot circuits have been designed to stay on for approximately 30 ns. The maximum capacitance of the lumped load that can be driven also depends directly on the one-shot duration. With very heavy capacitive loads, the one-shot can time-out before the signal is driven fully to the positive rail. The one-shot duration has been set to best optimize trade-offs between dynamic I_{CC}, load driving capability, and maximum bit-rate considerations. Both PCB trace length and connectors add to the capacitance of the TXS0108E output. Therefore, TI recommends that this lumped-load capacitance is considered in order to avoid one-shot retriggering, bus contention, output signal oscillations, or other adverse system-level affects.

9.3.4 Enable and Disable

The TXS0108E has an OE pin input that is used to disable the device by setting the OE pin low, which places all I/Os in the Hi-Z state. The disable time (t_{dis}) indicates the delay between the time when the OE pin goes low and when the outputs actually get disabled (Hi-Z). The enable time (t_{en}) indicates the amount of time the design must allow for the one-shot circuitry to become operational after the OE pin goes high.

9.3.5 Pull-up or Pull-down Resistors on I/O Lines

The TXS0108E has the smart pull-up resistors dynamically change value based on whether a low or a high is being passed through the I/O line. Each A-port I/O has a pull-up resistor (R_{PUA}) to V_{CCA} and each B-port I/O has a pull-up resistor (R_{PUB}) to V_{CCB} . R_{PUA} and R_{PUB} have a value of 40 k Ω when the output is driving low. R_{PUA} and R_{PUB} have a value of 4 k Ω when the output is driving high. R_{PUA} and R_{PUB} are disabled when OE = Low. This feature provides lower static power consumption (when the I/Os are passing a low), and supports lower V_{OL} values for the same size pass-gate transistor, and helps improve simultaneous switching performance.

9.4 Device Functional Modes

The TXS0108E device has two functional modes, enabled and disabled. To disable the device set the OE pin input low, which places all I/Os in a high impedance state. Setting the OE pin input high enables the device.

10 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The TXS0108E can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The device is ideal for use in applications where an open-drain driver is connected to the data I/Os. The device is appropriate for applications where a push-pull driver is connected to the data I/Os, but the TXB0104 device, (SCES650) 4-Bit Bidirectional Voltage-Level Translator might be a better option for such push-pull applications. The device is a semi-buffered auto-direction-sensing voltage translator design is optimized for translation applications (for example, MMC Card Interfaces) that require the system to start out in a low-speed open-drain mode and then switch to a higher speed push-pull mode.

10.2 Typical Application

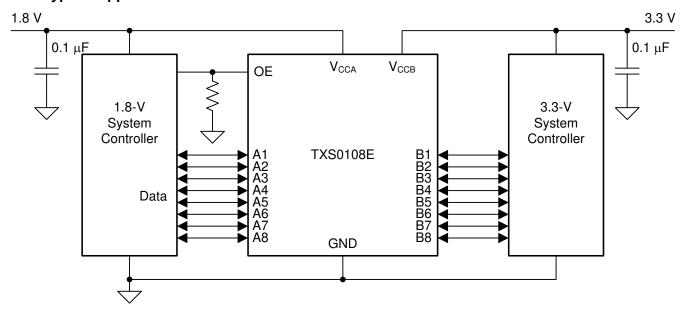


Figure 10-1. Typical Application Circuit

10.2.1 Design Requirements

For this design example, use the parameters listed in Table 10-1. Ensure that $V_{CCA} \le V_{CCB}$.

Table 10-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	1.4 V to 3.6 V
Output voltage range	1.65 V to 5.5 V

10.2.2 Detailed Design Procedure

To begin the design process, determine the following:

· Input voltage range



- Use the supply voltage of the device that is driving the TXS0108E device to determine the input voltage range. For a valid logic high the value must exceed the V_{IH} of the input port. For a valid logic low the value must be less than the V_{IL} of the input port.
- Output voltage range
 - Use the supply voltage of the device that the TXS0108E device is driving to determine the output voltage range.
 - The TXS0108E device has smart internal pull-up resistors. External pull-up resistors can be added to reduce the total RC of a signal trace if necessary.
- An external pull-down resistor decreases the output VOH and VOL. Use Equation 1 to calculate the VOH as a result of an external pull-down resistor.

$$V_{OH} = V_{CCX} \times R_{PD} / (R_{PD} + 4 k\Omega) \tag{1}$$

10.2.3 Application Curves

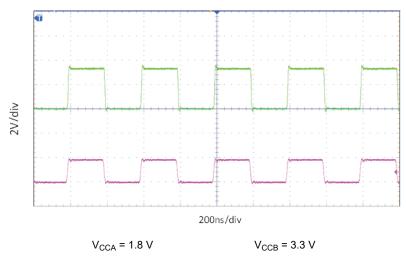


Figure 10-2. Level-Translation of a 2.5-MHz Signal

10.3 Power Supply Recommendations

During operation, ensure that $V_{CCA} \le V_{CCB}$ at all times. The sequencing of each power supply will not damage the device during the power up operation, so either power supply can be ramped up first. The output-enable (OE) input circuit is designed so that it is supplied by V_{CCA} and when the (OE) input is low, all outputs are placed in the high-impedance state. To ensure the high-impedance state of the outputs during power up or power down, the OE input pin must be tied to GND through a pull-down resistor and must not be enabled until V_{CCA} and V_{CCB} are fully ramped and stable. The minimum value of the pull-down resistor to ground is determined by the current-sourcing capability of the driver.

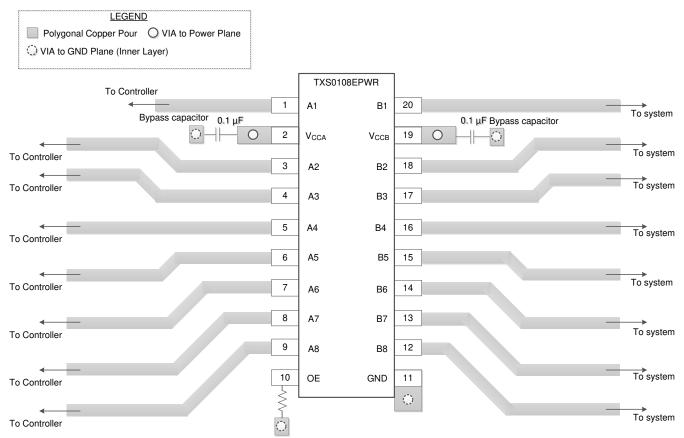
10.4 Layout

10.4.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines is recommended.

- Bypass capacitors should be used on power supplies. Place the capacitors as close as possible to the VCCA,
 VCCB pin and GND pin.
- Short trace lengths should be used to avoid excessive loading.
- PCB signal trace-lengths must be kept short enough so that the round-trip delay of any reflection is less than the one shot duration, approximately 30 ns, ensuring that any reflection encounters low impedance at the source driver.

10.4.2 Layout Example



Keep OE low until V_{CCA} and V_{CCB} are powered up

Figure 10-3. Layout Example



11 Device and Documentation Support

11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

- 1. Texas Instruments, Application Note, A guide to Voltage level translation using TXS devices
- 2. Texas Instruments, Application Note, Factors affecting the Vol of TXS AutoBidirectional Devices
- 3. Texas Instruments, Application Note, Effects of Pullup and Pulldown resistors on TXS Devices

11.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

11.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

25-Jul-2023 www.ti.com

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TXS0108ENMER	ACTIVE	NFBGA	NME	20	2500	RoHS & Green	(6) SNAGCU	Level-2-260C-1 YEAR	-40 to 85	2APW	Samples
TXS0108EPWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF08E	Samples
TXS0108EPWRG4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF08E	Samples
TXS0108ERGYR	ACTIVE	VQFN	RGY	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YF08E	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and



PACKAGE OPTION ADDENDUM

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continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TXS0108E:

Automotive: TXS0108E-Q1

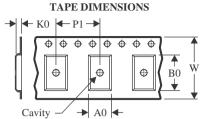
NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

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TAPE AND REEL INFORMATION

REEL DIMENSIONS Reel Diameter Reel Width (W1)



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

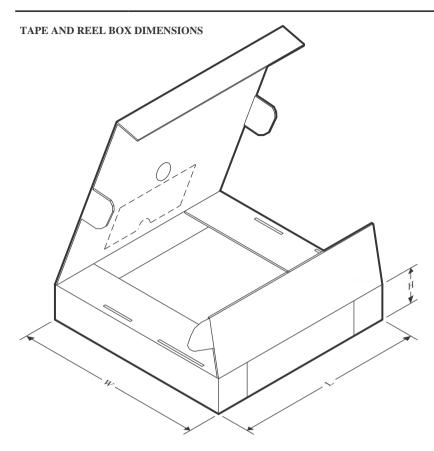
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TXS0108ENMER	NFBGA	NME	20	2500	330.0	12.4	2.85	3.4	1.34	4.0	12.0	Q2
TXS0108EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
TXS0108ERGYR	VQFN	RGY	20	3000	330.0	12.4	3.8	4.8	1.6	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TXS0108ENMER	NFBGA	NME	20	2500	336.6	336.6	31.8
TXS0108EPWR	TSSOP	PW	20	2000	356.0	356.0	35.0
TXS0108ERGYR	VQFN	RGY	20	3000	356.0	356.0	35.0



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



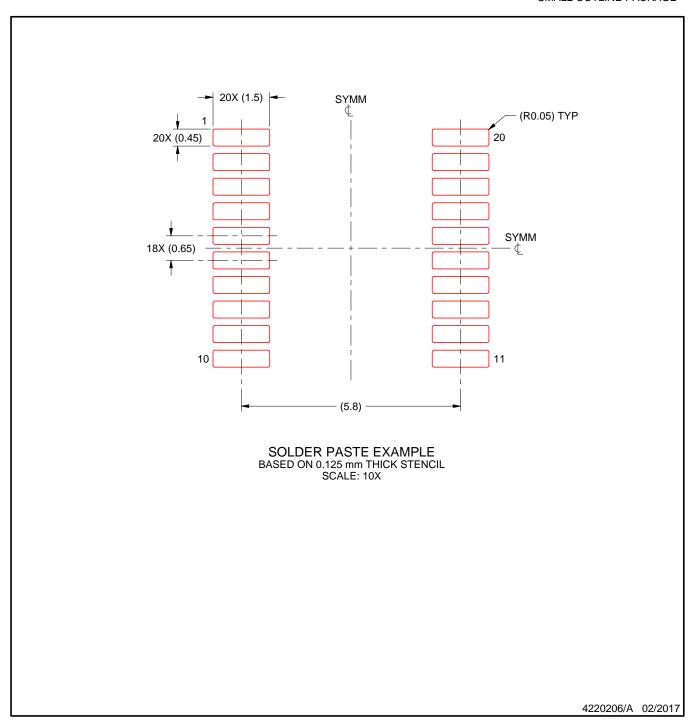
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

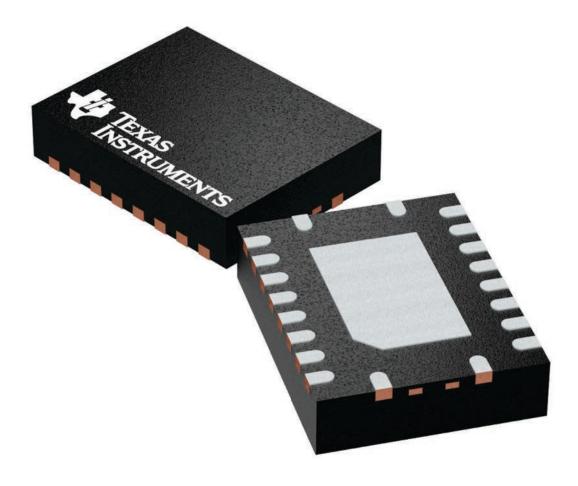
- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



3.5 x 4.5, 0.5 mm pitch

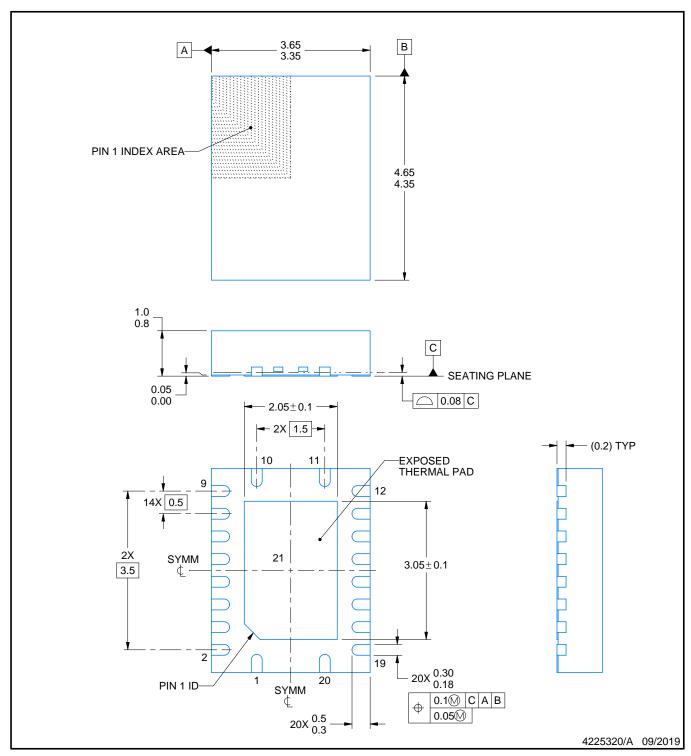
PLASTIC QUAD FGLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC QUAD FLATPACK - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

PLASTIC QUAD FLATPACK - NO LEAD

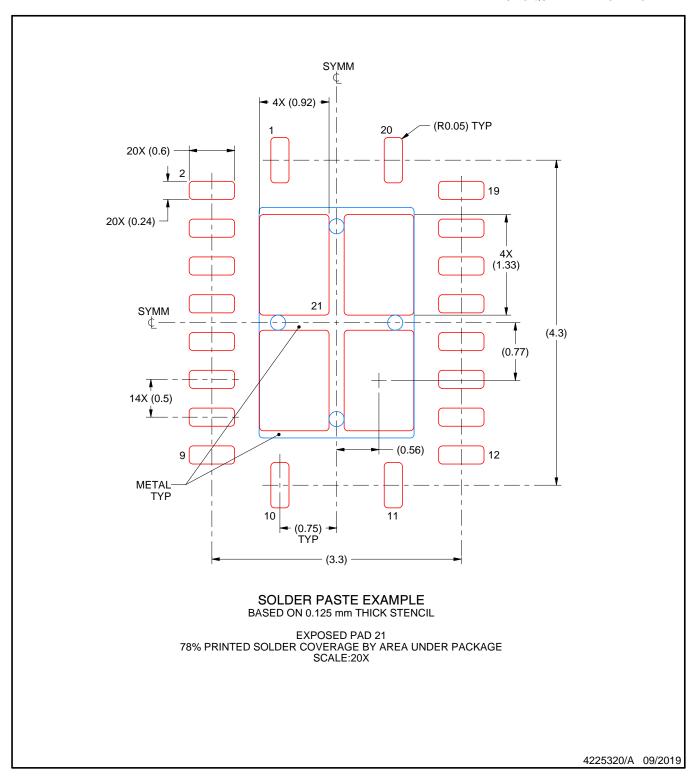


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD

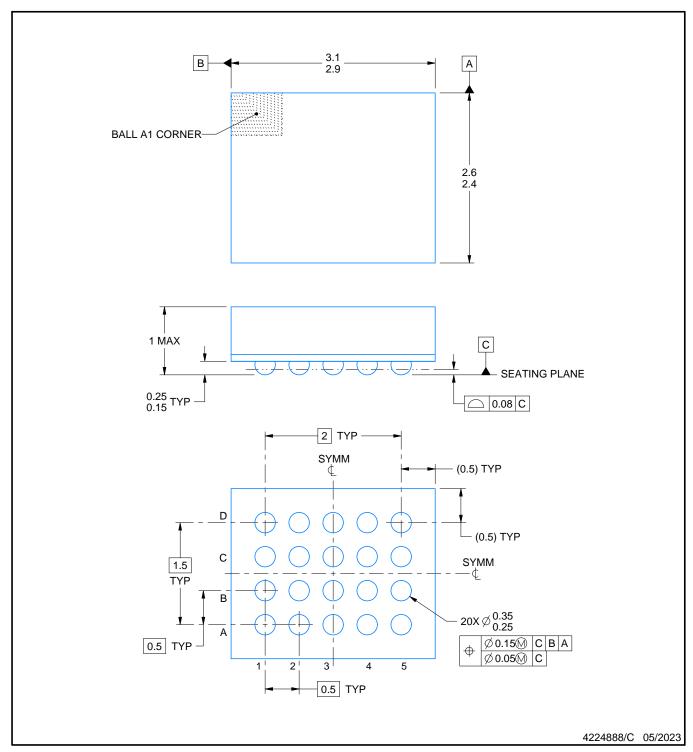


NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



PLASTIC BALL GRID ARRAY



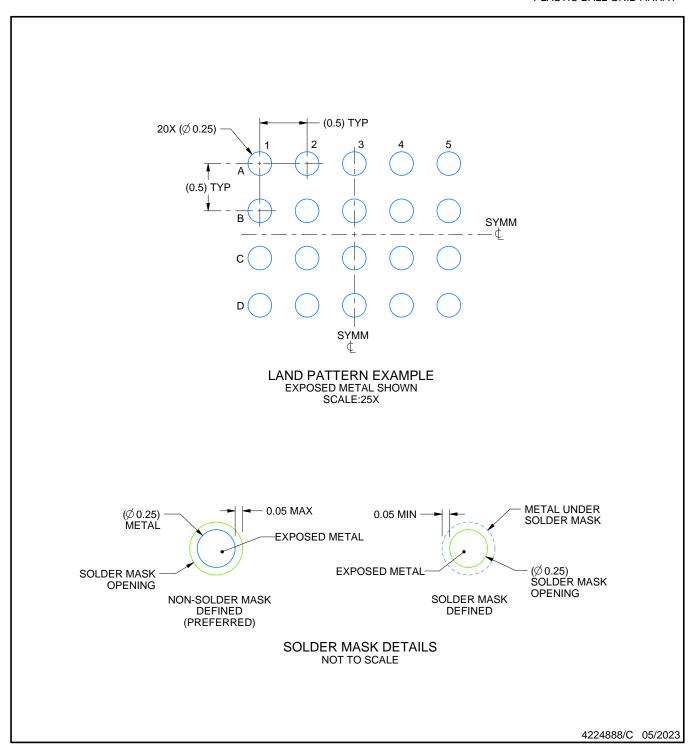
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



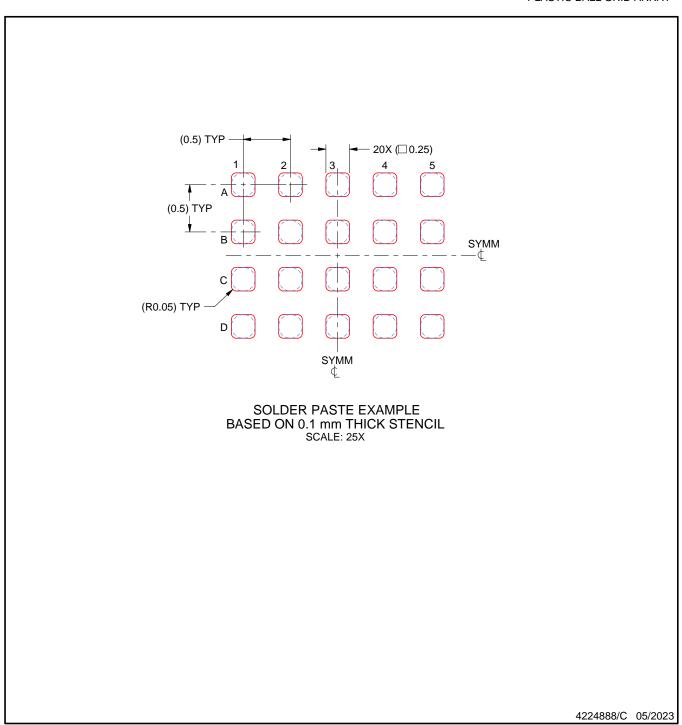
PLASTIC BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For information, see Texas Instruments literature number SPRAA99 (www.ti.com/lit/spraa99).

PLASTIC BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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